## Analog Frequency Multiplier

## PL660 and PL663 XO Families

## DESCRIPTION

PhaseLink's Analog Frequency Multipliers ${ }^{\text {TM }}$ (AFMs) are the industry's first "Balanced Oscillator" utilizing analog multiplication of the fundamental frequency (at double or quadruple frequency), combined with an attenuation of the fundamental of the reference crystal, without using a phase-locked loop (PLL), in CMOS technology.

PhaseLink's patent pending PL66x family of AFM products can achieve up to 800 MHz differential PECL, LVDS, or single-ended CMOS output with little jitter or phase noise deterioration.

PL66x-xx family of products utilize a low-power CMOS technology and are housed in GREEN/ RoHS compliant 16-pin TSSOP and $3 \times 3$ QFN packages.

## FEATURES

- Non-PLL frequency multiplication
- Input frequency from $30-200 \mathrm{MHz}$
- Output frequency from $60-800 \mathrm{MHz}$
- Low phase noise and jitter (equivalent to fundamental at the output frequency)
- Ultra-low jitter
- RMS phase jitter < 0.25 ps ( 12 kHz to 20 MHz )
- RMS period jitter < 2.5 ps typ.
- Low phase noise
- $-145 \mathrm{dBc} / \mathrm{Hz}$ @ 100 kHz offset from 155.52 MHz
- $-150 \mathrm{dBc} / \mathrm{Hz} @ 10 \mathrm{MHz}$ offset from 155.52 MHz
- Low input frequency eliminates the need for expensive crystals
- Differential PECL/LVDS, or single-ended CMOS output
- Single 2.5 V or $3.3 \mathrm{~V}+/-10 \%$ power supply
- Optional industrial temperature range $\left(-40^{\circ} \mathrm{C}\right.$ to $\left.+85^{\circ} \mathrm{C}\right)$
- Available in 16-pin GREEN/RoHS compliant TSSOP, and 16-pin 3x3 QFN packages.


Figure 1: 2X AFM Phase Noise at $\mathbf{2 1 2 . 5} \mathbf{~ M H z}$ ( $106.25 \mathrm{MHz} 3^{\text {rd }}$ overtone crystal)

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Figure 2: Block Diagram of AFM XO
Figure 3 shows the period jitter histogram of the $2 x$ Analog Frequency Multiplier at 212.5 MHz , while Figure 4 shows the very low levels of sub-harmonics that correspond to the exceptional performance (i.e. low jitter).


Figure 3: Period Jitter Histogram at 212.5MHz Analog Frequency Multiplier (2x), with 106.25 MHz crystal


Figure 4: Spectrum Analysis at 212.5 MHz
Analog Frequency Multiplier (2x), with sub-harmonics below -69 dBc

OE LOGIC SELECTION

| OUTPUT | OESEL | OE | Output State |
| :---: | :---: | :---: | :---: |
| PECL | 0 (Default) | 0 (Default) | Enabled |
|  |  | 1 | 1 |
|  |  |  |
|  |  | 0 | Tri-state |
|  | 0 (Default) | 1 (Default) | Enabled |
|  |  | 0 | Tri-state |
|  |  | 1 (Default) | Enabled |
|  |  | 0 (Default) | Enabled |

OESEL and OE: Connect to VDD to set to " 1 ", connect to GND to set to " 0 ". [The 'Default' state is set by internal pull up/down resistor.]

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## PRODUCT SELECTOR GUIDE

## FREQUENCY VERSUS PHASE NOISE PERFORMANCE

| Part <br> Number | Input Frequency Range (MHz) | Analog <br> Frequency Multiplication Factor | Output Frequency Range (MHz) | Output Type | Phase Noise at Frequency Offset From Carrier ( $\mathrm{dBc} / \mathrm{Hz}$ ) |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | Carrier Freq. (MHz) | 10 Hz | $\begin{gathered} 100 \\ \mathrm{~Hz} \end{gathered}$ | 1 KHz | $\begin{gathered} 10 \\ \mathrm{KHz} \end{gathered}$ | $\begin{aligned} & 100 \\ & \text { KHz } \end{aligned}$ | $\begin{gathered} 1 \\ \mathrm{MHz} \end{gathered}$ | $\begin{gathered} 10 \\ \mathrm{MHz} \end{gathered}$ |
| PL660-08 | 30-80 | 4 | 120-320 | PECL | 155.52 | -72 | -100 | -125 | -132 | -142 | -147 | -149 |
| PL660-09 | 30-80 | 4 | 120-320 | LVDS | 155.52 | -72 | -100 | -125 | -132 | -142 | -147 | -149 |
| PL663-07 | 30-80 | 2 | 60-160 | CMOS | 156.25 | -75 | -105 | -130 | -140 | -145 | -150 | -150 |
| PL663-08 | 30-80 | 2 | 60-160 | PECL | 156.25 | -75 | -105 | -130 | -140 | -145 | -150 | -150 |
| PL663-09 | 30-80 | 2 | 60-160 | LVDS | 156.25 | -75 | -105 | -130 | -140 | -145 | -150 | -150 |
| PL663-17 | 75-140 | 2 | 150-280 | CMOS | 212.5 | -70 | -100 | -130 | -140 | -145 | -148 | -148 |
| PL663-18 | 75-140 | 2 | 150-280 | PECL | 212.5 | -70 | -100 | -130 | -140 | -145 | -148 | -148 |
| PL663-19 | 75-140 | 2 | 150-280 | LVDS | 212.5 | -70 | -100 | -130 | -140 | -145 | -148 | -148 |
| PL663-28 | 140-160 | 2 | 280-320 | PECL | 311.04 | -60 | -92 | -122 | -140 | -142 | -146 | -146 |
| PL663-29 | 140-160 | 2 | 280-320 | LVDS | 311.04 | -60 | -92 | -122 | -140 | -142 | -146 | -148 |

FREQUENCY VERSUS JITTER, AND SUB-HARMONIC PERFORMANCE

| Part Number | Output Freq. (MHz) | RMS Period Jitter (ps) |  |  | Peak to Peak Period Jitter (ps) |  |  | RMS <br> Accumulated (L.T.) Jitter (ps) |  |  | Phase Jitter ( $12 \mathrm{KHz}-20 \mathrm{MHz}$ ) (ps) |  |  | Spectral Specifications / Sub-harmonic Content (dBc) <br> Frequency (MHz) |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | Carrier Freq. MHz (Fc) | $\begin{gathered} @ \\ -75 \% \\ \text { (Fc) } \end{gathered}$ | $\begin{gathered} \text { @ } \\ -50 \% \\ \text { (Fc) } \end{gathered}$ | $\begin{gathered} @ \\ -25 \% \\ \text { (Fc) } \end{gathered}$ | $\begin{gathered} \text { @ } \\ +25 \% \\ (\mathrm{Fc}) \end{gathered}$ | $\begin{gathered} @ \\ +50 \% \\ (\mathrm{Fc}) \end{gathered}$ | $\begin{gathered} \text { @ } \\ +75 \% \\ \text { (Fc) } \end{gathered}$ |
| PL660-08 | 155.52 |  | 3 | 5 |  | 21 | 30 |  |  | 5 |  | 0.25 |  | 155.52 | -66 | -61 |  |  | -67 | -70 |
| PL660-09 | 155.52 |  | 3 | 5 |  | 21 | 30 |  |  | 5 |  | 0.25 |  | 155.52 | -66 | -61 |  |  | -67 | -70 |
| PL663-07 | 156.25 |  | 2 | 3 |  | 18 | 20 |  |  | 3 |  | 0.24 |  | 156.25 |  | -70 |  |  | -75 |  |
| PL663-08 | 156.25 |  | 2 | 3 |  | 18 | 20 |  |  | 3 |  | 0.24 |  | 156.25 |  | -70 |  |  | -75 |  |
| PL663-09 | 156.25 |  | 2 | 3 |  | 18 | 20 |  |  | 3 |  | 0.24 |  | 156.25 |  | -70 |  |  | -75 |  |
| PL663-17 | 212.50 |  | 2.5 | 4 |  | 18 | 20 |  |  | 4 |  | 0.19 |  | 212.50 |  | -70 |  |  | -75 |  |
| PL663-18 | 212.50 |  | 2.5 | 4 |  | 18 | 20 |  |  | 4 |  | 0.19 |  | 212.50 |  | -70 |  |  | -75 |  |
| PL663-19 | 212.50 |  | 2.5 | 4 |  | 18 | 20 |  |  | 4 |  | 0.19 |  | 212.50 |  | -70 |  |  | -75 |  |
| PL663-28 | 311.04 |  | 2.5 | 4 |  | 18 | 20 |  |  | 4 |  | 0.16 |  | 311.04 |  | -65 |  |  | -70 |  |
| PL663-29 | 311.04 |  | 2.5 | 4 |  | 18 | 20 |  |  | 4 |  | 0.16 |  | 311.04 |  | -65 |  |  | -70 |  |

Note: Wavecrest data 10,000 hits. No Filtering was used in Jitter Calculations.
Agilent E5500 was used for phase jitter measurements.
Spectral specifications were obtained using Agilent E7401A.

## BOARD LAYOUT CONSIDERATIONS



To minimize parasitic effects and improve performance, do the following:

- Place the crystal as close as possible to the IC.
- Make the board traces that are connected to the crystal pins symmetrical. The board trace symmetry is very important, as it reduces the negative parasitic effects to produce clean frequency multiplication with low jitter.


## CRYSTAL SPECIFICATIONS

| Part Number | Crystal Resonator Frequency ( $\mathrm{F}_{\mathrm{XIN}}$ ) | Mode | CL (xtal) | $E S R\left(R_{E)}\right.$ | CO | C0/C1 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Typical | Max. | Max. | Max. |
| $\begin{aligned} & \text { PL660-08 } \\ & \text { PL660-09 } \end{aligned}$ | 25~75MHz | Fundamental or 3rd overtone | 5 pF | $30 \Omega$ | 4.5 pF | N.A. |
| $\begin{aligned} & \text { PL663-07 } \\ & \text { PL663-08 } \\ & \text { PL663-09 } \end{aligned}$ | $30 \sim 80 \mathrm{MHz}$ | Fundamental or 3rd overtone | 5 pF | $30 \Omega$ | 4.5 pF | N.A. |
| $\begin{aligned} & \text { PL663-17 } \\ & \text { PL663-18 } \\ & \text { PL663-19 } \end{aligned}$ | 75~140MHz | Fundamental or 3rd overtone | 5 pF | $60 \Omega$ | 4.0 pF | N.A. |
| $\begin{aligned} & \text { PL663-28 } \\ & \text { PL663-29 } \end{aligned}$ | 140~200MHz | Fundamental or 3rd overtone | 5 pF | $60 \Omega$ | 4.0 pF | N.A. |

[^0]
## EXTERNAL COMPONENT VALUES

## INDUCTOR VALUE OPTIMIZATION

The required inductor value(s) for the best performance depends on the operating frequency, and the board layout specifications. The listed values in this datasheet are based on the calculated parasitic values from PhaseLink's evaluation board design. These inductor values provide the user with a starting point to determine the optimum inductor values. Additional fine-tuning may be required to determine the optimal solution.

To assist with the inductor value optimization, PhaseLink has developed the "AFM Tuning Assistant" software. You can download this software from PhaseLink's web site (www.phaselink.com). The software consists of two worksheets. The first worksheet (named L2) is used to fine-tune the 'L2' inductor value, and the second worksheet (named L4) is used for fine tuning of the 'L4' (used in $4 x$ AFMs only) inductor value.

For those designs using PhaseLink's recommended board layout, you can use the "AFM Tuning Assistant" to determine the optimum values for the required inductors. This software is developed based on the parasitic information from PhaseLink's board layout and can be used to determine the required inductor and parallel capacitor (see LWB1 and Cstray parameters) values. For those employing a different board layout in their design, we recommend to use the parasitic information of their board layout to calculate the optimized inductor values. Please use the following fine tuning procedure:


Figure 5: Diagram Representation of the Related System Inductance and Capacitance

## DIE SIDE

- Cinternal = Based on AFM Device
- Cpad $=2.0 \mathrm{pF}$, Bond pad and its ESD circuitry
- C11 = 0.4 pF , The following amplifier stage


## PCB side

- LWB1 = 2 nH , (2 places), Stray inductance
- Cstray $=1.0 \mathrm{pF}$, Stray capacitance
- L2X (L4X) $=2 x$ or $4 x$ inductor
- C2X (C4X) = range (0.1 to 2.7), Fine tune inductor if used


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- There are two default variables that normally will not need to be modified. These are Cpad, and C11 and are found in cells B22 and B27 of 'AFM Tuning Assistant', respectively.
- LWB1 is the combined stray inductance in the layout. The DIE wire bond is $\sim 0.6 \mathrm{nH}$ and in the case of a leaded part an additional 1.0 nH is added. Your layout inductance must be added to these. There are 2 of these and they are assumed to be approximately symmetrical so you only need to enter this inductance once in cell B23.
- Enter the stray parasitic capacitance into cell B26. An additional 0.5 pF must be added to this value if a leaded part is used.
- Enter the appropriate value for Cinternal into B21 based on the device used (see column D). Use the 'AFM Tuning Assistant' software to calculate L2X (and C2X if used) for your resonance frequency.
- For 4X AFMs, repeat the same procedure in the L4X worksheet.
- See the examples below.


## DETERMINING STRAY L's AND C's IN A LAYOUT



Figure 6: Diagram Representation of PL660-08 Board Layout
Let's take the PL660-08 ( $4 \times \mathrm{XO}$ ) for example, as shown in Figure 6. This takes a crystal input range of 30 to 80 MHz and multiplies this to an output of 120 to 320 MHz . To determine the stray L's and C's of the layout we will assemble two test units. One AFM will be tuned to the lower range of the device ( 120 MHz ), and the other to the upper range of the device ( 320 MHz ).

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120 MHz AFM Tuning: Using the "AFM Tuning Assistant" find the PL660-0x in the L2X worksheet. Enter the Cinternal value found next to it into cell B21. In cell B24 enter the closest standard inductor value (see CoilCraft 0603CS series for example) to achieve the closest peak frequency to 60 MHz . Repeat the same procedure for L 4 X at 120 MHz .
Results: L2X = $180 \mathrm{nH}, \mathrm{L} 4 \mathrm{X}=\mathbf{8 2} \mathbf{n H}$.
320 MHz AFM tuning: Repeat the previous procedure for L 2 X at 120 MHz and L 4 X at 320 MHz .
Results: L2X = 24 nH , L4X = 10 nH .
Proceed and assemble the test units.
Measuring 120 MHz L2X: Connect the RF generator and scope probe as shown in Figure 6. While power is applied to the PCB, set the generator output to +12 dBm and the frequency to 30 MHz . Since this is the $2 x$ port, the scope will show 60 MHz with ~ 3 V pk-pk amplitude. Vary the generator above and below 30 MHz until the amplitude on the scope is maximum and record the generator frequency. For example peak recorded at $29.8 \times 2$ or 59.6 MHz.

Measuring 320 MHz L2X: Connect the RF generator and scope probe as shown in Figure 6. While power is applied to the PCB, set the generator output to +12 dBm and the frequency to 80 MHz . Since this is the $2 x$ port the scope will show 160 MHz with ~ 3 V pk-pk amplitude. Vary the generator above and below 80 MHz until the amplitude on the scope is maximum and record the generator frequency. For example peak recorded at $78.0 \times 2=$ 156 MHz

In the AFM Tuning Assistant, add the scope's probe capacitance to the Cstray cell. For our example $0.5 \mathrm{pF}+1.0$ $\mathrm{pF}=1.5 \mathrm{pF}$. With L2X at 24 nH adjust LWB1 (cell B23) until the peak frequency reads 156 MHz . Next replace the L2X value with 180 nH and see if it peaks at 59.6 MHz . If it does not, adjust the Cstray until 59.4 MHz is achieved. Again enter 24 nH for L2X and fine tune LWB1 for 156 MHz .

Results: LWB1 = 1.6 nH , Cstray $=2.9 \mathrm{pF}-0.5 \mathrm{pF}=2.4 \mathrm{pF}$ (subtract scope probe stray)
Repeat the same steps for the L4X: Set the generator to 80 MHz . The 82 nH peaks at 118 MHz and the 10 nH peaks at 304 MHz .

Results: LWB1 = 1.8 nH , Cstray $=2.5 \mathrm{pF}-0.5 \mathrm{pF}=2.0 \mathrm{pF}$ (subtract scope probe stray)

| Internal Capacitor Selection by Device |  |  |
| :---: | :---: | :---: |
| Device Number | Cinternal (pF) |  |
|  | 2X | 4X |
| PL660-0X | 34.125 | 16.500 |
| PL663-0X | 46.500 |  |
| PL663-1X | 14.625 |  |
| PL663-2X | 14.625 |  |

## PL660 and PL663 XO Families

 EXTERNAL COMPONENT VALUES - $3^{\text {RD }}$ OVERTONE RESISTOR SELECTIONS (R3rd)This resistor is only required when a third overtone crystal is used. The chart below indicates the calculated and the nearest "E12" resistor values versus frequency.

| PL660-08/09 |  | PL663-07/08/09 |  | PL663-017/18/19 |  | PL663-28/29 |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Freq. <br> $\mathbf{( M H z )}$ | R3rd <br> $\mathbf{( \Omega )}$ | E12 <br> Pick <br> K $\boldsymbol{\Omega}$ | Freq. <br> $\mathbf{( M H z )}$ | R3rd <br> $\mathbf{( \Omega )}$ | E12 <br> Pick <br> K $\boldsymbol{\Omega}$ | Freq. <br> $\mathbf{( M H z )}$ | R3rd <br> $\mathbf{( \Omega )}$ | E12 <br> Pick <br> K $\boldsymbol{\Omega}$ | Freq. <br> $\mathbf{( M H z )}$ | R3rd <br> $\mathbf{( \Omega )}$ | E24 <br> Pick <br> K $\boldsymbol{\Omega}$ |
| 24 | 12,396 | 12 | 30 | 9,917 | 10 | 75 | 2,125 | 2.2 | 140.0 | 915 | 0.91 |
| 26 | 11,442 | 12 | 32 | 9,297 | 10 | 77.5 | 2,056 | 2.2 | 142.0 | 902 | 0.91 |
| 28 | 10,625 | 10 | 34 | 8,750 | 8.2 | 80 | 1,992 | 2.2 | 144.0 | 890 | 0.91 |
| 30 | 9,917 | 10 | 36 | 8,264 | 8.2 | 82.5 | 1,932 | 1.8 | 146.0 | 878 | 0.91 |
| 32 | 9,297 | 10 | 38 | 7,829 | 8.2 | 85 | 1,875 | 1.8 | 148.0 | 866 | 0.91 |
| 34 | 8,750 | 8.2 | 40 | 7,438 | 6.8 | 87.5 | 1,821 | 1.8 | 150.0 | 854 | 0.82 |
| 36 | 8,264 | 8.2 | 42 | 7,083 | 6.8 | 90 | 1,771 | 1.8 | 152.0 | 843 | 0.82 |
| 38 | 7,829 | 8.2 | 44 | 6,761 | 6.8 | 92.5 | 1,723 | 1.8 | 154.0 | 832 | 0.82 |
| 40 | 7,438 | 6.8 | 46 | 6,467 | 6.8 | 95 | 1,678 | 1.8 | 156.0 | 821 | 0.82 |
| 42 | 7,083 | 6.8 | 48 | 6,198 | 6.8 | 97.5 | 1,635 | 1.5 | 158.0 | 811 | 0.82 |
| 44 | 6,761 | 6.8 | 50 | 5,950 | 5.6 | 100 | 1,594 | 1.5 | 160.0 | 801 | 0.82 |
| 46 | 6,467 | 6.8 | 52 | 5,721 | 5.6 | 102.5 | 1,555 | 1.5 | 162.0 | 790 | 0.82 |
| 48 | 6,198 | 6.8 | 54 | 5,509 | 5.6 | 105 | 1,518 | 1.5 | 164.0 | 780 | 0.75 |
| 50 | 5,950 | 5.6 | 56 | 5,313 | 5.6 | 107.5 | 1,483 | 1.5 | 166.0 | 770 | 0.75 |
| 52 | 5,721 | 5.6 | 58 | 5,129 | 4.7 | 110 | 1,449 | 1.5 | 168.0 | 759 | 0.75 |
| 54 | 5,509 | 5.6 | 60 | 4,958 | 4.7 | 112.5 | 1,417 | 1.5 | 170.0 | 749 | 0.75 |
| 56 | 5,313 | 5.6 | 62 | 4,798 | 4.7 | 115 | 1,386 | 1.5 | 172.0 | 740 | 0.75 |
| 58 | 5,129 | 4.7 | 64 | 4,648 | 4.7 | 117.5 | 1,356 | 1.5 | 174.0 | 730 | 0.75 |
| 60 | 4,958 | 4.7 | 66 | 4,508 | 4.7 | 120 | 1,328 | 1.2 | 176.0 | 720 | 0.75 |
| 62 | 4,798 | 4.7 | 68 | 4,375 | 4.7 | 122.5 | 1,301 | 1.2 | 178.0 | 711 | 0.68 |
| 64 | 4,648 | 4.7 | 70 | 4,250 | 3.9 | 125 | 1,275 | 1.2 | 180.0 | 701 | 0.68 |
| 66 | 4,508 | 4.7 | 72 | 4,132 | 3.9 | 127.5 | 1,250 | 1.2 | 182.0 | 692 | 0.68 |
| 68 | 4,375 | 4.7 | 74 | 4,020 | 3.9 | 130 | 1,226 | 1.2 | 184.0 | 683 | 0.68 |
| 70 | 4,250 | 3.9 | 76 | 3,914 | 3.9 | 132.5 | 1,203 | 1.2 | 186.0 | 674 | 0.68 |
| 72 | 4,132 | 3.9 | 78 | 3,814 | 3.9 | 135 | 1,181 | 1.2 | 188.0 | 665 | 0.68 |
| 74 | 4,020 | 3.9 | 80 | 3,719 | 3.9 | 137.5 | 1,159 | 1.2 | 190.0 | 656 | 0.68 |
| 76 | 3,914 | 3.9 |  |  |  | 140 | 1,138 | 1.2 | 192.0 | 647 | 0.62 |
|  |  |  |  |  |  |  |  |  | 194.0 | 639 | 0.62 |
|  |  |  |  |  |  |  |  |  | 196.0 | 630 | 0.62 |
|  |  |  |  |  |  |  |  |  | 198.0 | 622 | 0.62 |
|  |  |  |  |  |  |  |  |  | 200.0 | 614 | 0.62 |

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## ELECTRICAL SPECIFICATIONS

## ABSOLUTE MAXIMUM RATINGS

| PARAMETERS | SYMBOL | MIN. | MAX. | UNITS |
| :--- | :---: | :---: | :---: | :---: |
| Supply Voltage | $\mathrm{V}_{\mathrm{DD}}$ |  | 4.6 | V |
| Input Voltage, DC | $\mathrm{V}_{\mathrm{I}}$ | $\mathrm{GND}-0.5$ | $\mathrm{~V}_{\mathrm{DD}}+0.5$ | V |
| Output Voltage, DC | $\mathrm{V}_{\mathrm{O}}$ | $\mathrm{GND}-0.5$ | $\mathrm{~V}_{\mathrm{DD}}+0.5$ | V |
| Storage Temperature | $\mathrm{T}_{\mathrm{S}}$ | -55 | +150 | ${ }^{\circ} \mathrm{C}$ |
| Industrial Ambient Operating Temperature | $\mathrm{T}_{\mathrm{A}_{-}}$ | -40 | +85 | ${ }^{\circ} \mathrm{C}$ |
| Commercial Ambient Operating Temperature | $\mathrm{T}_{\mathrm{A}_{-} \mathrm{C}}$ | 0 | +70 | ${ }^{\circ} \mathrm{C}$ |
| Junction Temperature | $\mathrm{T}_{\mathrm{J}}$ |  | 125 | ${ }^{\circ} \mathrm{C}$ |
| Lead Temperature (soldering, 10s) |  |  | 260 | ${ }^{\circ} \mathrm{C}$ |

Exposure of the device under conditions beyond the limits specified by Maximum Ratings for extended periods may cause permanent damage to the device and affect product reliability. These conditions represent a stress rating only, and functional operations of the device at these or any other conditions above the operational limits noted in this specification is not implied.

## PECL ELECTRICAL CHARACTERISTICS

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Supply Current (with loaded outputs) | IDD | Fout $=212.5 \mathrm{MHz}$ | 58 | 65 | 75 | mA |
| Operating Supply Voltage | VDD |  | 2.25 |  | 3.63 | V |
| Output Clock Duty Cycle |  | @ V $\mathrm{VDD}^{\text {- }} 1.3 \mathrm{~V}$ | 45 | 50 | 55 | \% |
| Short Circuit Current |  |  |  | $\pm 50$ |  | mA |
| Output High Voltage | Vor | $\begin{gathered} \mathrm{R}_{\mathrm{L}}=50 \Omega \text { to } \\ \mathrm{V}_{\mathrm{DD}}-2 \mathrm{~V} \end{gathered}$ | $V_{D D}-1.025$ |  |  | V |
| Output Low Voltage | Vol | $\mathrm{R}_{\mathrm{L}}=50 \Omega$ to $\mathrm{V}_{\mathrm{DD}}-2 \mathrm{~V}$ |  |  | $\begin{aligned} & \hline V_{D D}- \\ & 1.620 \\ & \hline \end{aligned}$ | V |
| Clock Rise Time | $\mathrm{tr}_{r}$ | @20/80\% |  | 0.25 | 0.45 | ns |
| Clock Fall Time | $t_{f}$ | @80/20\% |  | 0.25 | 0.45 | ns |



## Analog Frequency Multiplier

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LVDS ELECTRICAL CHARACTERISTICS

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Supply Current (with loaded outputs) | IDD | Fout $=212.5 \mathrm{MHz}$ |  | 55 | 60 | mA |
| Operating Supply Voltage | VDD |  | 2.25 |  | 3.63 | V |
| Output Clock Duty Cycle |  | @ 1.25V | 45 | 50 | 55 | \% |
| Output Differential Voltage | Vod | $\begin{aligned} & R_{L}=100 \Omega \\ & \text { (see figure) } \end{aligned}$ | 247 | 355 | 454 | mV |
| VDD Magnitude Change | $\Delta \mathrm{V}_{\text {OD }}$ |  | -50 |  | 50 | mV |
| Output High Voltage | Vor |  |  | 1.4 | 1.6 | V |
| Output Low Voltage | Vol |  | 0.9 | 1.1 |  | V |
| Offset Voltage | Vos |  | 1.125 | 1.2 | 1.375 | V |
| Offset Magnitude Change | $\Delta \mathrm{Vos}$ |  | 0 | 3 | 25 | mV |
| Power-off Leakage | loxd | $\begin{gathered} V_{\text {out }}=V_{D D} \text { or } G N D \\ V_{D D}=0 V \end{gathered}$ |  | $\pm 1$ | $\pm 10$ | $\mu \mathrm{A}$ |
| Output Short Circuit Current | losd |  |  | -5.7 | -8 | mA |
| Differential Clock Rise Time | $\mathrm{tr}_{r}$ | $\begin{aligned} & R_{L}=100 \Omega \\ & C_{L}=10 \mathrm{pF} \\ & \text { (see figure) } \\ & \hline \end{aligned}$ | 0.2 | 0.5 | 0.7 | ns |
| Differential Clock Fall Time | $t_{f}$ |  | 0.2 | 0.5 | 0.7 | ns |

LVDS Transistion Time Waveform


## Analog Frequency Multiplier

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## CMOS ELECTRICAL CHARACTERISTICS

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Supply Current, Dynamic, with Loaded Outputs | IDD | At 100 MHz , load=15pF |  | 32 | 40 | mA |
| Operating Supply Voltage | $V_{D D}$ |  | 2.25 |  | 3.63 | V |
| Output High Voltage (LVTTL) | Vон3. 3 | $\mathrm{I}_{\text {OH }}=-8.5 \mathrm{~mA}, 3.3 \mathrm{~V}$ Supplies | 2.4 |  |  | V |
| Output Low Voltage (LVTTL) | Vol3. 3 | $\mathrm{loL}=8.5 \mathrm{~mA}, 3.3 \mathrm{~V}$ Supplies |  |  | 0.4 | V |
| Output High Voltage (LVCMOS) | Vонс3.3 | $\mathrm{I}_{\text {он }}=-4 \mathrm{~mA}, 3.3 \mathrm{~V}$ Supplies | VDD - 0.4 |  |  | V |
| Output High Voltage | Vor2. 5 | $\mathrm{I}_{\text {OH }}=1 \mathrm{~mA}, 2.5 \mathrm{~V}$ Supplies | $V_{D D}-0.2$ |  |  | V |
| Output Low Voltage | Vol2.5 | $\mathrm{loL}=1 \mathrm{~mA}, 2.5 \mathrm{~V}$ Supplies |  |  | 0.2 | V |
| Output drive current | losd | $\mathrm{V}_{\mathrm{OL}}=0.4 \mathrm{~V}, \mathrm{~V}_{\mathrm{OH}}=2.4 \mathrm{~V}$ <br> (per output) |  | 8.5 |  | mA |
| Output Clock Rise/Fall Time | $\mathrm{T}_{\mathrm{r}} \mathrm{T}_{\mathrm{f}}$ | $\begin{aligned} & 10 \% \sim 90 \% \text { VDD with } 10 \mathrm{pF} \\ & \text { load } \end{aligned}$ |  | 1.2 | 1.6 | ns |
| Output Clock Duty Cycle |  | Measured @ 50\% VDD | 45 | 50 | 55 | \% |
| Short Circuit Current | Is |  |  | $\pm 50$ |  | mA |

Analog Frequency Multiplier
PL660 and PL663 XO Families

## BOARD DESIGN AND LAYOUT CONSIDERATIONS

L2X and L4X: Reduce the PCB trace inductance to a minimum by placing L2X and L4X as physically close to their respective pins as possible. Also be sure to bypass each $V_{D D}$ connection especially taking care to place a 0.01 $u F$ bypass at the $V_{D D}$ side of $L 2 X$ and $L 4 X$ (see recommended layout).

Crystal Connections: Be sure to keep the ground plane under the crystal connections continuous so that the stray capacitace is consistent on both crystal connections. Also be sure to keep the crystal connections symmetrical with respect to one another and the crystal connection pins of the IC. If you chose to use a series capacitance and/or inductor to fine tune the crystal frequency, be sure to put symmetrical pads for this cap on both crystal pins (see Cadj in recommended layout), even if one of the capacitors will be a 0.01 uF and the other is used to tune the frequency. To further maintain a symmetrical balance on a crystal that may have more internal Cstray on one pin or the other, place capacitor pads (Cbal) on each crystal lead to ground (see recommended layout). R3rd is only required if a $3^{\text {rd }}$ overtone crystal is used.
$V_{D D}$ and GND: Bypass VDDANA and VDDBUF with separate bypass capacitors and if a $V_{D D}$ plane is used, feed each bypass cap with its own via. Be sure to connect any ground pin including the bypass caps with short via connection to the ground plane.

OESEL: J 1 is recommended so the same PCB layout can be used for both OESEL settings.


PL660 (4x AFM) TSSOP Layout


PL663 (2x AFM) TSSOP Layout

## PACKAGE PIN DESCRIPTION AND ASSIGNMENT



2x AFM Package Pin Out
4x AFM Package Pin Out
PIN ASSIGNMENTS

| Name | Pin \# | Type | Product | Description |
| :---: | :---: | :---: | :---: | :---: |
| DNC | 1 | 1 | 2 X | Do Not Connect. |
| OSCOFFSEL |  |  | 4X | Set to "0" (GND) to turn off the oscillator when outputs are disabled (OE). Default (no connect) is OSC always on. |
| GNDOSC | 2 | P | 2 X \& 4X | GND connection for oscillator. |
| DNC | 3 | 1 | 2 X \& 4 X | Do Not Connect. |
| XIN | 4 | 1 | 2 X \& 4 X | Input from crystal oscillator circuitry. |
| XOUT | 5 | 0 | 2 X \& 4X | Output from crystal oscillator circuitry. |
| OE | 6 | 1 | 2 X \& 4 X | Output Enable input. See "OE LOGIC SELECTION TABLE". |
| DNC | 7 | 1 | 2 X | Do Not Connect. |
| L4X |  |  | 4X | External inductor connection. The inductor is recommended to be a high Q small size 0402 or 0603 SMD component, and must be placed between L4X and adjacent VDDOSC. Place inductor as close to the IC as possible to minimize parasitic effects and to maintain inductor Q . This inductor is used with $4 x$ AFMs. |
| GNDANA | 8 | P | 2 X | GND connection. |
| VDDOSC |  |  | 4X | VDD connection for oscillator circuitry. VDDOSC should be separately decoupled from other VDDs whenever possible. |
| GNDBUF | 9 | P | 2 X \& 4X | GND connection. |
| Q | 10 | 0 | 2 X \& 4X | PECL/LVDS/CMOS output. |
| QBAR | 11 | 0 | 2 X \& 4X | Complementary PECL/LVDS output or in-phase CMOS. |
| VDDBUF | 12 | P | 2X \& 4X | VDD connection for output buffer circuitry. VDDBUF should be separately decoupled from other VDDs whenever possible. |
| OESEL | 13 | I | 2 X | Selector input to choose the OE control logic (see "OE SELECTION TABLE"). If no connection is applied, value will be set to default through internal pull-down resistor. |
|  | 14 |  | 4X |  |
| VDDANA | 14 | P | 2X | VDD connection for analog circuitry.VDDANA should be separately decoupled from other VDDs whenever possible. |
|  | 13 |  | 4X |  |
| VDDOSC | 15 | P | 2 X \& 4X | VDD connection for oscillator. VDD should be separately decoupled from other VDDs whenever possible. |
| L2X | 16 | 1 | 2X \& 4X | External inductor connection. The inductor is recommended to be a high Q small size 0402 or 0603 SMD component, and must be placed between L2X and adjacent VDDOSC. Place inductor as close to the IC as possible to minimize parasitic effects and to maintain inductor $Q$. |

Note: 663-xx devices are $2 x$ multipliers, and 660-xx devices are $4 x$ multipliers.

## Analog Frequency Multiplier

PL660 and PL663 XO Families

## PACKAGE INFORMATION

16 PIN TSSOP

| 16 PIN TSSOP ( mm ) |  |  |
| :---: | :---: | :---: |
| Symbol | Min. | Max. |
| A | - | 1.20 |
| A1 | 0.05 | 0.15 |
| B | 0.19 | 0.30 |
| C | 0.09 | 0.20 |
| D | 4.90 | 5.10 |
| E | 4.30 | 4.50 |
| H | 6.40 BSC |  |
| L | 0.45 | 0.75 |
| e | 0.65 BSC |  |



16 PIN 3x3 QFN


## ORDERING INFORMATION



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[^0]:    Note: Non-specified parameters can be chosen as standard values from crystal suppliers.
    CL ratings larger than 5 pF require a crystal frequency adjustment.
    Request detailed crystal specifications from PhaseLink.

